

Department of Humanities and Sciences

Course File

APPLIED PHYSICS (Course Code: AP202BS)

I B.Tech II Semester

2023-24

Dr.Ummar Pasha Dr. Sivanagi Reddy Emani Dr.Ujwal P Prabhu





APPLIED PHYSICS

Check List

S. No	Name of the Format	Page No.
1	Syllabus	1
2	Timetable	3
3	Vision & Mission of Institute and Department	4
3	Program Educational Objectives	5
4	Program Outcomes	5
5	Course Objectives	6
6	Course Outcomes	6
7	Guidelines to study the course	7
8	Course Schedule	8
9	Course Plan	10
10	Lesson Plan	14
11	Assignment Sheets	38
12	Tutorial Sheets	43
13	Evaluation Strategy	48
14	Course completion status	49
15	Assessment in relation to CO's and CO's	50
16	Mappings of CO's and PO's	50
17	Rubric for course	51
18	Mid-I and Mid-II question papers	52
19	Mid-I & Mid-II mark	56
20	Sample answer scripts and Assignments	65
21	Course materials like Notes, PPT's, etc.	82



Int. Marks:40 Ext. Marks:60 Total Marks:100

Applied Physics (AP202BS)

(Common for all branches)

Course Code: AP202BS

UNIT-I: WAVE OPTICS

Huygen's principle, superposition of waves, interference, interference in thin films by Reflection, Newton's rings (theory & experiment), diffraction, types of diffraction, Farunhofer diffraction at single slit, plane diffraction gratings, resolving power of grating, polarization, polarization by reflection, polarization by double refraction, Nicol's prism.

UNIT - II: QUANTUM PHYSICS AND SOLIDS

Quantum Physics: blackbody radiation and Planck's law (Qualitative), De Broglie hypothesis, Davisson – Germer experiment, Heisenberg uncertainty principle (Qualitative), Born interpretation of the wave function, time independent Schrodinger wave equation, particle in one dimensional potential box.

Solids: free electron theory (Drude & Lorentz, Sommerfeld) (Qualitative), Bloch's theorem, Kronig-Penney model (Qualitative), E-K diagram, effective mass of electron, origin of energy bands, classification of solids.

UNIT - III: SEMICONDUCTORS AND DEVICES

Intrinsic and extrinsic semiconductors, energy band diagrams, Hall effect, direct and indirect band gap semiconductors, Formation of P-N junction diode, energy level diagram of P-N junction, V-I characteristics of P-N Junction, Zener diode and bipolar junction transistor (BJT), Construction, working and characteristics of LED, photo diode and solar cell.

UNIT - IV: NANOTECHNOLOGY

Nanoscale, quantum confinement, surface to volume ratio, bottom-up fabrication: sol-gel, combustion methods, top-down fabrication: ball milling. physical vapor deposition (PVD), Chemical vapor deposition (CVD), Characterization techniques - XRD, SEM &TEM, applications of nanomaterials.

UNIT - V: LASER AND FIBER OPTICS

Lasers: Interaction of radiation with matter: Absorption, Spontaneous emission and stimulated emission, Einstein coefficients and their relations, Laser beam characteristics, important components of laser-active medium, pumping source, optical resonator, Construction and working



principle- Nd: YAG laser, He-Ne laser, semiconductor laser, applications of laser.

Fiber Optics: Introduction to optical fiber, advantages of optical fibers, total internal reflection, construction of optical fiber, acceptance angle, numerical aperture, classification of optical fibersstep index and graded index optical fiber, losses in optical fiber, optical fiber for communication system, applications of optical fiber.

TEXT BOOKS:

- 1. M. N. Avadhanulu, P.G. Kshirsagar & TVS Arun Murthy" A Text book of Engineering Physics"- S. Chand Publications, 11/e 2019.
- 2. Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson Publication, 2019
- 3. P.K. Palanisamy A Text Book of Engineering Physics, Scietech Publications.

REFERENCE BOOKS:

- 1. Halliday, Resnick and Walker, Fundamentals of Physics, John Wiley & Sons, 11th Edition, 2018.
- 2. B.K. Pandey and S. Chaturvedi, Engineering Physics, Cengage Learning, 2ndEdition, 2022.
- Essentials of Nanoscience & Nanotechnology by Narasimha Reddy Katta, Typical CreativesNANO DIGEST, 1st Edition, 2021
- 4. A.K. Katiyar, C. K. Pandey Engineering Physics 2/e, Wiley India pvt Ltd.2017.



2. Timetable

I B.Tech. II Semester – CSE (A Sec)

Day/Hour	9.30- 10.20	10.20- 11.10	11.20- 12.10	12.10- 12.50	12.50- 1.35	1.35- 2.20	2.30-3.15	3.15-4.00
Monday		AP						
Tuesday		AP						
Wednesday	AP							
Thursday					AP			
Friday		AP						
Saturday		AP						

I B.Tech. II Semester – CSE (B Sec)

Day/Hour	9.30- 10.20	10.20- 11.10	11.20- 12.10	12.10- 12.50	12.50- 1.35	1.35- 2.20	2.30-3.15	3.15-4.00
Monday	AP							
Tuesday					AP			
Wednesday						AP		
Thursday		AP						
Friday					AP			
Saturday			AP					

I B.Tech. II Semester – CSE (C Sec)

Day/Hour	9.30-10.20	10.20-11.10	11.20-12.10	12.50-1.35	1.35-2.20	2.30-3.15	3.15-4.00
Monday					AP		
Tuesday				AP			
Wednesday		AP					
Thursday						AP	
Friday					AP		
Saturday		AP LAB					AP



Vision of the Institute

To be a premier Institute in the country and region for the study of Engineering, Technology and Management by maintaining high academic standards which promotes the analytical thinking and independent judgment among the prime stakeholders, enabling them to function responsibly in the globalized society.

Mission of the Institute

To be a world-class Institute, achieving excellence in teaching, research and consultancy in cutting-edge Technologies and be in the service of society in promoting continued education in Engineering, Technology and Management.

Quality Policy

To ensure high standards in imparting professional education by providing world-class infrastructure, topquality-faculty and decent work culture to sculpt the students into Socially Responsible Professionals through creative team-work, innovation and research.

Vision of the Department

To foster the students with excellence in education and moral values, thereby transform them to be eminent professional engineers and responsible citizens of tomorrow.

Mission of the Department

To metamorphosis the students' community to get conversant with Scientific, Mathematical concepts and communication skills by providing perpetual thought provoking teaching, tremendous training and relentless research.



Program Educational Objectives (B.Tech. - CSE)

Graduates will be able to

- **PEO 1:** Excel in professional career and/or higher education by acquiring knowledge in mathematical, computing and engineering principles.
- **PEO 2:** Be able to analyze the requirements of the software, understand the technical specifications, design and provide novel engineering solutions and efficient product designs.
- PEO 3: Adopt professionalism, ethical attitude, communication skills, team work, lifelong learning in their profession.

Program Outcomes (B.Tech. –CSE)

At the end of the Program, a graduate will have the ability to

- PO 1: Gain an ability to apply knowledge of mathematics, science and engineering fundamentals appropriate to the discipline.
- PO 2: Develop the competence to identify, analyze, formulate and solve engineering problems.
- PO 3: Acquire an ability to design, implement, and evaluate a computer-based system, process, component, or program to meet desired needs with appropriate consideration for public health and safety, cultural, societal and environmental considerations.
- PO 4: Are capable of design and conduct experiments, analyze and interpret data in the field of computer science and engineering.
- PO 5: Gain expertise to use the techniques, skills and modern engineering tools with proficiency in the basic area of computer science and engineering.
- PO 6: An ability to analyze the local and global impact of computing on individuals, organizations, and society.
- PO 7: Knowledge of contemporary issues
- PO 8: Sensitive to engage in activities with conscious social responsibility adhering to ethical values.
- PO 9: An ability to function effectively individually and on teams, including diverse and multidisciplinary, to accomplish a common goal.
- PO 10: An ability to articulate professional ideas clearly and precisely in making written and oral presentations.
- PO 11: Recognition of the need for and an ability to engage in continuing professional development.
- PO 12: An understanding of engineering and management principles and apply these to one's own work, as a member and leader in a team, to manage projects.



COURSE OBJECTIVES

On completion of this Subject/Course the student shall be able to:

S.No	Objectives
1	Understand the phenomenon of diffraction, interference and polarization
2	Recognize the basic principles of quantum physics and band theory of solids
3	Understand the underlying mechanism involved in construction and working principles of various semiconductor devices
4	Identify the importance of nanoscale, quantum confinement and various fabrications techniques.
5	Study the characteristics of lasers and optical fibers

COURSE OUTCOMES

The expected outcomes of the Course/Subject are:

S.No	Outcomes
1.	Understand various optical phenomena of light
2.	Apply basic the principles of quantum mechanics to classify solids based on band theory.
3.	Identify the role of semiconductor devices in science and engineering Applications.
4.	Understand the features and applications of Nanomaterial's in various fields
5.	Understand various aspects of Lasers and Optical fiber and their applications in diverse fields.

Dr. SK. Ummar. Pashe - 100 Dr. Sivanagi Reddy Emani - 25 Dr. U.U.Prabhy - 111

Signature of faculty

Note: Please refer to Bloom's Taxonomy, to know the illustrative verbs that can be used to state the outcomes.



GUIDELINES TO STUDY THE COURSE / SUBJECT

Course Design and Delivery System (CDD):

- The Course syllabus is written into number of learning objectives and outcomes.
- Every student will be given an assessment plan, criteria for assessment, scheme of evaluation and grading method.
- The Learning Process will be carried out through assessments of Knowledge, Skills and Attitude by various methods and the students will be given guidance to refer to the text books, reference books, journals, etc.

The faculty be able to –

- Understand the principles of Learning
- Understand the psychology of students
- Develop instructional objectives for a given topic
- Prepare course, unit and lesson plans
- Understand different methods of teaching and learning
- Use appropriate teaching and learning aids
- Plan and deliver lectures effectively
- Provide feedback to students using various methods of Assessments and tools of Evaluation
- Act as a guide, advisor, counselor, facilitator, motivator and not just as a teacher alone



Signature of HOD Date:5-2-2024

Dr. Sk. Ummar Pasha - U Dr. Sivanagi Reddy Emani - & Dr. U U Prabhy -

Signature of faculty Date:5-2-2024



COURSE SCHEDULE

The Schedule for the whole Course / Subject is:

S. No.	Description	Duration	n (Date)	Total No.
5.110.	Description	From	То	of Periods
1.	Unit-I: WAVE OPTICS Huygen's principle, superposition of waves, interference, interference in thin films by Reflection, Newton's rings (theory & experiment), diffraction, types of diffraction, Farunhofer diffraction at single slit, plane diffraction gratings, resolving power of grating, polarization, polarization by reflection, polarization by double refraction, Nicol's prism	5.2.2024	22.2.2024	14
2.	Unit-II: QUANTUM PHYSICS AND SOLIDS Quantum Physics: blackbody radiation and Planck's law (Qualitative), De Broglie hypothesis, Davisson – Germer experiment, Heisenberg uncertainty principle (Qualitative), Born interpretation of the wave function, time independent Schrodinger wave equation, particle in one dimensional potential box. Solids: free electron theory (Drude & Lorentz, Somerfield) (Qualitative), Bloch's theorem, Kronig-Penney model (Qualitative), E-K diagram, effective mass of electron, origin of energy bands, classification of solids	23.2.2024	12.3.2024	14
3.	Unit-III: SEMICONDUCTORS AND DEVICES Intrinsic and extrinsic semiconductors, energy band diagrams, Hall effect, direct and indirect band gap semiconductors, Formation of P-N junction diode, energy level diagram of P-N junction, V-I characteristics of P-N Junction, Zener diode and bipolar junction transistor (BJT), Construction, working and characteristics of LED, photo diode and solar cell	16.3.2024	25.4.2024	10
4.	Unit-IV: NANOTECHNOLOGY Nanoscale, quantum confinement, surface to volume ratio, bottom-up fabrication: sol-gel, combustion methods, top-down fabrication: ball milling. physical vapor deposition (PVD), Chemical vapor deposition (CVD), Characterization techniques - XRD, SEM &TEM, applications of nanomaterials	26.4.2024	4.5.2024	12
5.	Unit-V: LASER AND FIBER OPTICS Lasers: Interaction of radiation with matter: Absorption, Spontaneous emission and stimulated emissio, Einstein coefficients and their relations, Laser beam characteristics, important components of laser-active medium, pumping source, optical resonator, Construction and working principle-	6.5.2024	12.6.2024	13



Nd:YAG laser, He- Ne laser, semiconductor laser, applications		
of laser.		
Fiber Optics: Introduction to optical fiber, advantages of		
optical fibers, total internal reflection, construction of optical		
fiber, acceptance angle, numerical aperture, classification of		
optical fibers- step index and graded index optical fiber, losses		
in optical fiber, optical fiber for communication system,		
applications of optical fiber.		

Total No. of Instructional periods available for the course: 63 Hours + 2hr (Mid-I Exam)



SCHEDULE OF INSTRUCTIONS - COURSE PLAN

Unit No.	Lesson No.	Date	No. of Periods	Topics / Sub-Topics	Objectives & Outcomes Nos.	References (Textbook, Journal)
	1	8.2.2024 9.2.2024	2	Course Introduction, Huygen's principle	1 1	A.K. Katiyar, C. K. Pandey Engineering Physics 2/e Wiley India Pvt Ltd., 2017
	2	12.2.2024 13.2.2024	2	superposition of waves, Interference	1 1	A.K. Katiyar, C. K. Pandey Engineering Physics 2/e Wiley India Pvt Ltd., 2017
	3	14.2.2024 15.2.2024 16.3.2024	3	Interference in thin films by Reflection, Newton's rings (theory & experiment),	1 1	A.K. Katiyar, C. K. Pandey Engineering Physics 2/e Wiley India Pvt Ltd., 2017
1.	4	17.2.2024	1	diffraction, types of diffraction	1 1	A.K. Katiyar, C. K. Pandey Engineering Physics 2/e Wiley India Pvt Ltd., 2017
	5	19.2.2024	2	Fraunhofer diffraction at single slit, plane diffraction gratings	1 1	A.K. Katiyar, C. K. Pandey Engineering Physics 2/e Wiley India Pvt Ltd., 2017
	6	20.2.2024	1	resolving power of grating,	1	A.K. Katiyar, C. K. Pandey Engineering Physics 2/e Wiley India Pvt Ltd., 2017
	7	21.2.2024	1	polarization, polarization by reflection, polarization by double refraction	1	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
	8	22.2.2024	2	Nicol's prism	1 1	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
	1	23.2.2024 24.2.2024	2	blackbody radiation and Planck's law (Qualitative), De Broglie hypothesis,	2 2	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
	2	26.2.2024	1	Davisson – Germer experiment	2 2	A.K. Katiyar, C. K. Pandey Engineering Physics 2/e Wiley India Pvt Ltd., 2017
2.	3	27.2.2024	1	Heisenberg uncertainty principle (Qualitative), Born interpretation of the wave function	2 2	A.K. Katiyar, C. K. Pandey Engineering Physics 2/e Wiley India Pvt Ltd., 2017
	4	28.2.2024	1	time independent Schrodinger wave equation	2 2	A.K. Katiyar, C. K. Pandey Engineering Physics 2/e Wiley India Pvt Ltd., 2017
	5	29.2.2024 1.3.2024	2	particle in one dimensional potential box.	2 2	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e 2019
	6	2.3.2024 5.3.2024	2	free electron theory (Drude & Lorentz, Sommerfeld)	2 2	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e 2019



r	1	· · · ·	Dep	artment of Humanities and	Sciences	· · · · · · · · · · · · · · · · · · ·
	7	6.3.2024 11.3.2024	2	Bloch's theorem, Kronig-Penney model (Qualitative),	2 2	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e 2019
	8	12.3.2024	1	E-K diagram, effective mass of electron,	2 2	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e 2019
	9	14.3.2024 15.3.2024	1	origin of energy bands, classification of solids.	2 2	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e 2019
	1	16.3.2024 19.3.2024	1	Intrinsic and extrinsic semiconductors, energy band diagrams, direct and indirect band gap semiconductors	3 3	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e 2019
	2	27.3.2024	1	Hall effect	3 3	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e 2019
	3	30.3.2024	1	Revision	1,2.3 1,2,3	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e 2019
		1.4.2024	2			
	4	10.4.2023	1	PN junction diode	3 3	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e 2019
3.	5	23.4.2024	1	Zener diode	3 3	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand , 11/e 2019
	6	24.4.2024	2	bipolar junction transistor (BJT)	3 3	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand , 11/e 2019
	7	25.4.2024	1	Construction, working and characteristics of LED	3 3	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand , 11/e 2019
	8	26.4.2024	1	Construction, working and characteristics of photo diode	3 3	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand , 11/e 2019
	9	26.4.2024	1	Construction, working and characteristics of solar cell	3 3	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand , 11/e 2019
4	1	27.4.2024	2	Nanoscale, quantum confinement, surface to volume ratio,	4 4	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand , 11/e 2019
	2	29.4.2024	2	Bottom-up fabrication: sol gel, combustion methods	4 4	M. N. Avadhanulu, A Text book of Engineering Physics"



		1	Dep	ai tinent of flumanties and	Defences	
						S. Chand , 11/e 2019
	3	30.4.2024	2	Top-down fabrication: ball milling	4 4	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand , 11/e 2019
	4	1.5.25024	2	Physical vapor deposition (PVD)	4 4	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand , 11/e 2019
	5	3.5.2024	1	Chemical vapor deposition (CVD)	4 4	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand , 11th Edition 2019
	6	3.5.2024	1	Characterization techniques - XRD	4 4	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11th 2019
	7	4.5.2024	1	Scanning Electron Microscope (SEM)	4 4	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e, 2019
	8	4.5.2024	1	Transmission Electron Microscope (TEM), Applications of nanomaterials	4 4	M. N. Avadhanulu, A Text book of Engineering Physics" S. Chand, 11/e, 2019
	1	6.5.2024	2	Interaction of radiation with matter: Absorption, Spontaneous emission and stimulated emission,	5 5	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
	2	7.5.2024	2	Einstein coefficients and their relations Laser beam characteristics	5 5	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
	3	8.5.2024	1	Important components of laser-active medium, pumping source, optical resonator	5 5	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
5	4	9.5.2024	1	Construction and working principle- Nd: YAG laser, He-Ne laser	5 5	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
	5	9.5.2024	2	semiconductor laser applications of laser, Introduction to optical fiber advantages of optical fibers	5 5	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
	6	10.5.2024	1	total internal reflection construction of optical fiber	5 5	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
	7	4.6.2024 5.6.2024	2	acceptance angle, numerical aperture, classification of optical fibers- step index and graded index optical fiber	5	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019



8	6.06.2024 10.6.2024	2	losses in optical fiber, optical fiber for communication system,	5 5	Shatendra Sharma and Jyotsna Sharma, Engineering Physics, Pearson, 2019
			applications of optical fiber.		



Signature of HOD

Date:

Note:

- 1. Ensure that all topics specified in the course are mentioned.
- 2. Additional topics covered, if any, may also be specified in bold.
- 3. Mention the corresponding course objective and outcome numbers against each topic.

Dr. SK. Ummar Pasha - Un Dr. Sivanagi Reddy Emani - E Dr. U.U.Prabhy - Lift

Signature of faculty

Date:



LESSON PLAN (U-I)

Lesson No: 01, 02

Duration of Lessons: 3hr 20 min

Lesson Title: Interference

Instructional / Lesson Objectives:

- To make students understand course structure and phenomenon of wave optics
- To familiarize students on wave fronts and generation of interference
- To understand students the concept of interference.
- To provide information on conditions for interference.

Teaching AIDS

: PPTs, Black board

Time Management of Class : 200 minutes

15 mins for taking attendance15 mins for previous lecture150 min for the lecture delivery20 min for doubts session

Refer assignment – I & tutorial-I sheets

Da. Sk. Ummar Pasha - W Da. Si Vanagi Reddy Emari - & Da. U.U.Prabhy - A



LESSON PLAN (U-I)

Lesson No: 03, 04

Duration of Lesson: 3 hr20 min

Lesson Title: Interference and diffraction

Instructional / Lesson Objectives:

- To make students understand formation of newton rings and interference in thin films
- To familiarize students on formation of interference pattern
- To understand students the concept of diffraction.
- To provide information on types of diffraction and daily life examples.

Teaching AIDS	: PPTs, Black board
Time Management of Class	: 200 minutes

15 mins for taking attendance15 mins for previous lecture150 min for the lecture delivery20 min for doubts session

Refer assignment – I & tutorial-I sheets

Da. SK. Ummaz Pasha - U	
D.R. Si Vanagi Reddy Emani - 🖉	
D.s. U.U.Prabhy - Lifet	



LESSON PLAN (U-I)

Lesson No: 05, 06

Duration of Lesson: 2 hr30 min

Lesson Title: Diffraction & Polarization

Instructional / Lesson Objectives:

- To make students understand the concept of resolving power and polarization.
- To familiarize students on single slit and diffraction gratings.
- To understand students the diffraction at single slit &resolving power of grating.
- To provide information on methods of generation of polarized light

Teaching AIDS : PPTs, Black board

Time Management of Class: 150 min.

10 mins for taking attendance 20 for revision of previous class 100 min for lecture delivery 20 min for doubts session

Refer assignment – I & tutorial-I sheets

Da. SK. Ummaz Pasha - W
D.R. Sivanagi Reddy Emani -
Ds. UU.Prabhy - Mar



LESSON PLAN (U-I)

Lesson No: 07,08

Duration of Lesson: 2hr 30 min

Lesson Title: Nicol's prism

Instructional / Lesson Objectives:

- To make students understand working and applications of Nicol's prism.
- To familiarize students on polarization methods
- To understand students the concept of double refraction and total internal reflection
- To provide information on applications of polarizers.

Teaching AIDS : PPTs, Black board Time Management of Class : 150 min

05 mins for taking attendance10 min for revision of previous class.120 min for the lecture delivery15 min for doubts session

Refer assignment – I & tutorial-I sheets

Da. Sk. Ummaz Pasha - 1
D.R. Sivanagi Reddy Emani - 🕹
D.s. UU.Prabhy - Mar



LESSON PLAN (U-II)

Lesson No: 01,02 Duration of Lesson: 1hr30 MIN Lesson Title: blackbody radiation & Davisson – Germer experiment,

Instructional / Lesson Objectives:

- To make students understand the concept of black body radiation & dual nature of matter.
- To familiarize students on plank's law, de Broglie hypothesis
- To understand students' limitations of classical physics and dual nature of matter
- To provide information on Davission Germer experiment

Teaching AIDS: PPTs, Black boardTime Management of Class: 150 min.

5 mins for taking attendance10 min for revision of previous class.120 min for the lecture delivery15 min for doubts session

Refer assignment-II & tutorial-II sheets.

Da. SK. Ummaz Pasha - 🕪
D.R. Sivanagi Reddy Emani -
D.s. UU.Prabhy - Math



LESSON PLAN (U-II)

Lesson No: 03,04

Duration of Lesson: 1hr 40 min.

Lesson Title: Heisenberg uncertainty principle (Qualitative), Born interpretation of the wave function, time independent Schrodinger wave equation.

Instructional / Lesson Objectives:

- To make students understand Heisenberg uncertainty principle and TISWE.
- To familiarize students on HUP and TISEW.
- To understand students the concept of uncertainty and probability density of wave functions.
- To provide information on wave functions and TISWE.

Teaching AIDS: PPTs, Black boardTime Management of Class: 100 min.

10 mins for taking attendance10 min for revision of previous class70 min for the lecture delivery10 min for doubts session

Refer assignment-II & tutorial-II sheets.

Da. SK. Ummaz Pasha - Uni
D.R. Sivanagi Reddy Emani - 🖉
Dr. UU.Prabhy - Mat



LESSON PLAN (U-II)

Lesson No: 05

Duration of Lesson: 1hr 40 min.

Lesson Title: particle in one dimensional potential box.

Instructional / Lesson Objectives:

- To make students understand potential in quantum mechanics
- To familiarize students on one dimensional box and its significance.
- To understand students the concept of wave functions, quantization of energy.
- To provide information on energy levels and probability of finding electron in particular region.

Teaching AIDS	: PPTs, Black board
Time Management of Class	: 100 min.

10 mins for taking attendance10 min for revision of previous class70 min for the lecture delivery10 min for doubts session

Refer assignment-II & tutorial-II sheets.

Da. SK. Ummaz Pasha - 1
D.R. Sivanagi Reddy Emani - 👶
Ds. UU.Prabhy -



LESSON PLAN (U-II)

Lesson No: 06, 07,08

Duration of Lesson: 3 hr20 min

Lesson Title: free electron theory (Drude & Lorentz, Sommerfeld), Bloch's theorem, Kronig-Penney model (Qualitative),E-K diagram, effective mass of electron,

Instructional / Lesson Objectives:

- To make students understand the concept of free electron, periodic potential, effective mass
- To familiarize students on free electron theories and K-P model.
- To understand students the conduction of electrons in different materials.
- To provide information on solution for kronig-penny model and E-K diagram.

Teaching AIDS	: PPTs, Black board
Time Management of Class	: 200 min

15 mins for taking attendance15 mins for previous lecture150 min for the lecture delivery20 min for doubts session

Refer assignment-II & tutorial-II sheets.

Da. SK. Ummaz Pasha - 1
D.R. Sivanagi Reddy Emani -
D.s. U.U.Prabhy -



LESSON PLAN (U-II)

Lesson No: 09 Duration of Lesson: 50 min Lesson Title: origin of energy bands, classification of solids.

Instructional / Lesson Objectives:

- To make students understand origin of energy bands and classification of solids.
- To familiarize students on conduction and valence bands, conductors, semiconductors and insulators.
- To understand students the concept fermi level, acceptor and donor levels
- To provide information on band structures of materials.

Teaching AIDS : PPTs, Black board

Time Management of Class : 50 min

5 mins for taking attendance 5 mins for previous lecture 30 min for the lecture delivery 10 min for doubts session

Refer assignment-II & tutorial-II sheets.

Da. SK. Ummaz Pasha - 1
Dr. Sivanagi Reddy Emani - 🗟
D.s. UU.Prabhy - Mar



LESSON PLAN (U-IIII)

Lesson No: 01,02

Duration of Lesson: 2hr30 min

Lesson Title: Intrinsic and extrinsic semiconductors, energy band diagrams, Hall effect

Instructional / Lesson Objectives:

- To make students understand Hall effect
- To familiarize students on direct and indirect bandgap semiconductors
- To understand students the concept of doping to form intrinsic and extrinsic semiconductors.
- To provide information on structure and applications of semiconductors

Teaching AIDS	: PPTs, Black board
Time Management of Class	: 100 min

10 mins for taking attendance20 for revision of previous class60 min for lecture delivery10 min for doubts session

Refer assignment-III & tutorial-III sheets.

Da. SK. Ummaz Pasha - Uni
D.R. Sivanagi Reddy Emani - 🖉
Ds. UU.Prabhy -



LESSON PLAN (U-III)

Lesson No: 04

Duration of Lesson: 50 min

Lesson Title: pn junction diode

Instructional / Lesson Objectives:

- To make students understand the concept of diodes and biasing.
- To familiarize students on formation and working of pn junctions
- To understand students the difference between forward and reverse bias.
- To provide information on I- V Characteristics and applications of pn junction diode

Teaching AIDS: PPTs, Black boardTime Management of Class: 50 min

5 mins for taking attendance 5 mins for previous lecture 30 min for the lecture delivery 10 min for doubts session

Refer assignment-III & tutorial-III sheets.

Da. Sk. Ummaz Pasha - Uni
D.R. Sivanagi Reddy Emani - 🖉
Dr. UU.Prabhy - Life



LESSON PLAN (U-III)

Lesson No: 05,06

Duration of Lesson: 2hr 30 min

Lesson Title: Zener diode, Bipolar junction transistor (BJT)

Instructional / Lesson Objectives:

- To make students understand difference between pn and zenar diode.
- To familiarize students on functioning of n-p-n and p-n-p transistor.
- To understand students the concept of different working regions in BJT.
- To provide information on applications of diode and transistor.

Teaching AIDS : PPTs, Black board

Time Management of Class : 150 min

5 mins for taking attendance10 min for revision of previous class.120 min for the lecture delivery15 min for doubts session

Refer assignment-III & tutorial-III sheets.

Da. SK. Ummaz Pasha - Uni
D.R. Sivanagi Reddy Emaini - 🖉
D.s. U.U.Prabhy - upp



LESSON PLAN (U-III)

Lesson No: 07,08

Duration of Lesson: 1hr 40 min

Lesson Title: LED and Photo diode

Instructional / Lesson Objectives:

- To make students understand construction and working of LED and photodiode.
- To familiarize students on I-V characteristics of LED and photodiode.
- To understand students the concept of electroluminescence and photovoltaic effect.
- To provide information on applications of LED and Photodiode.

Teaching AIDS : PPTs, Black board Time Management of Class : 100 min

10 mins for taking attendance15 for revision of previous class60 min for lecture delivery15 min for doubts session

Refer assignment-III & tutorial-III sheets.

Da. Sk. Ummaz Pasha - 10	
D.R. Sivanagi Reddy Emani - 🖉	
Dr. UU.Prably - if	



LESSON PLAN (U-III)

Lesson No: 09

Duration of Lesson: 50 min

Lesson Title: Solar Cell

Instructional / Lesson Objectives:

- To make students understand the concept of photovoltaic effect and efficiency of solar cell'
- To familiarize students on construction and working of solar cell.
- To understand students the difference between solar cell and photodiode.
- To provide information on applications of solar cell.

Teaching AIDS: PPTs, Black boardTime Management of Class: 50 min.

5 mins for taking attendance5 mins for previous lecture30 min for the lecture delivery10 min for doubts session

Refer assignment-III & tutorial-III sheets.

Da. SK. Ummaz Pasha - V	
D.e. Si vanagi Reddy Emaini - 🖉	
D.s. UUPrably - if	



LESSON PLAN (U-IV)

Lesson No: 01, 02

Duration of Lesson: 2 hr 30 min

Lesson Title: Nano science and Bottom-up fabrication: sol-gel, combustion methods

Instructional / Lesson Objectives:

- To make students understand the synthesis methods of nanomaterials
- To familiarize students on nanoscale and significance of nanomaterials.
- To understand students the concept of quantum confinement, surface to volume ratio
- To provide information on sol-gel process and combustion methods.

Teaching AIDS	: PPTs, Black board
Time Management of Class	: 150 min

5 mins for taking attendance10 min for revision of previous class.120 min for the lecture delivery15 min for doubts session

Refer assignment - IV & tutorial-IV sheets

Da. SK. Ummaz Pasha - U
D.R. Sivanagi Reddy Emaini - 🖉
Dr. UU.Prabhy -



LESSON PLAN (U-IV)

Lesson No: 03, 04

Duration of Lesson: 3 hr20 min

Lesson Title: Top-down fabrication: ball milling, Physical vapor deposition (PVD)

Instructional / Lesson Objectives:

- To make students understand top down and bottom-up methods.
- To familiarize students on ball milling and PVD
- To understand students the concept of milling and vapor deposition.
- To provide information on advantages, limitation and applications of the method.

Teaching AIDS : PPTs, Black board

Time Management of Class : 200 min

15 mins for taking attendance15 mins for previous lecture150 min for the lecture delivery20 min for doubts session

Refer assignment – IV & tutorial-IV sheets

Da. Sk. Ummaz Pasha - 1
D.E. Sivanagi Reddy Emani - 🕹
D.s. UU.Prabhy -



LESSON PLAN (U-IV)

Lesson No: 05

Duration of Lesson: 1hr30 MIN

Lesson Title: Chemical vapor deposition (CVD)

Instructional / Lesson Objectives:

- To make students understand the concept of CVD
- To familiarize students on procedure to synthesize nanomaterials.
- To provide information on applications of CVD.

Teaching AIDS: PPTs, Black boardTime Management of Class: 50 min

5 mins for taking attendance 5 mins for previous lecture 30 min for the lecture delivery 10 min for doubts session

Refer assignment – IV & tutorial-IV sheets

Da. SK. Ummaz Pasha - 1	
D.R. Sivanagi Reddy Emani - 🖉	
Ds. UU.Prabhy - Life	



LESSON PLAN (U-IV)

Lesson No: 06, 07

Duration of Lesson: 1 hr 40 min

Lesson Title: Characterization techniques - XRD, SEM

Instructional / Lesson Objectives:

- To make students understand significance of characterization of nanomaterials.
- To familiarize students on characterization of nanomaterials using XRD and SEM
- To understand students the analysis of XRD and SEM diagrams of nanomaterials.
- To provide information on crystal structure analysis and morphological studies of nanomaterials.

Teaching AIDS: PPTs, Black boardTime Management of Class: 100 min

10 mins for taking attendance15 for revision of previous class60 min for lecture delivery15 min for doubts session

Refer assignment - IV & tutorial-IV sheets

Da. SK. Ummaz Pasha - Uni
D.R. Sivanagi Reddy Emaini - 🕹
Dr. UUPrabhy - Upt



LESSON PLAN (U-IV)

Lesson No: 08

Duration of Lesson: 50 min

Lesson Title: Transmission Electron Microscope (TEM), Applications of nanomaterials

Instructional / Lesson Objectives:

- To make students understand the construction and working of TEM
- To familiarize students on TEM image analysis
- To understand students the concept of single crystal, polycrystalline and amorphous
- To provide information on nanoparticle size distribution and defects in materials.

Teaching AIDS: PPTs, Black boardTime Management of Class: 50 min

5 mins for taking attendance5 mins for previous lecture30 min for the lecture delivery10 min for doubts session

Refer assignment – IV & tutorial-IV sheets

Da. SK. Ummaz Pasha - 1
D.R. Sivanagi Reddy Emani - 🖉
Dr. UU.Prabhy - up



LESSON PLAN (U-V)

Lesson No: 01,02

Duration of Lessons: 3hr 20 min

Lesson Title: Interaction of radiation with matter & Einstein coefficients and their relations

Instructional / Lesson Objectives:

- To make students understand the concept of absorption and stimulated emission
- To familiarize students on interaction of matter with radiation.
- To provide information on Einstein coefficients and relations.

Teaching AIDS	: PPTs, Black board
Time Management of Class	: 200 min

15 mins for taking attendance15 mins for previous lecture150 min for the lecture delivery20 min for doubts session

Refer assignment- V & tutorial-V sheets.

Da. SK. Ummaz Pasha - Un
D.R. Sivanagi Reddy Emani - 🖉
D.s. UU.Prabhy - Life



LESSON PLAN (U-V)

Lesson No: 03,04

Duration of Lesson: 1hr 40 min

Lesson Title: Laser beam characteristics, Important components of laser-active medium, pumping source, optical Resonator, Construction and working principle- Nd: YAG laser, He-Ne laser

Instructional / Lesson Objectives:

- To make students understand working of laser
- To familiarize students on components of laser and its functioning
- To understand students the concept of population inversion and lasing action
- To provide information on Construction and working of Lasers.

Teaching AIDS: PPTs, Black boardTime Management of Class: 100 min

10 mins for taking attendance15 for revision of previous class60 min for lecture delivery15 min for doubts session

Refer assignment- V & tutorial-V sheets.

Da. SK. Ummaz Pasha - 1
D.R. Sivanagi Reddy Emani - 🖉
Ds. UU.Prabhy -



LESSON PLAN (U-V)

Lesson No: 05

Duration of Lesson: 1hr40 min

Lesson Title: semiconductor laser and applications of laser,

Instructional / Lesson Objectives:

- To make students understand working of semiconductor laser.
- To familiarize students on laser characteristics and applications
- To provide information on applications of lasers in different fields.

Teaching AIDS: PPTs, Black boardTime Management of Class: 100 min

10 mins for taking attendance15 for revision of previous class60 min for lecture delivery15 min for doubts session

Refer assignment- V & tutorial-V sheets.

Da. Sk. Ummaz Pasha - 1
D.R. Sivanagi Reddy Emani - 🚳
Da. UU.Prabhy -

Signature of faculty



LESSON PLAN (U-V)

Lesson No: 06, 07

Duration of Lesson: 2hr30 min

Lesson Title: Introduction to optical fibers and classification

Instructional / Lesson Objectives:

- To make students understand the concept of total internal reflection, acceptance angle and numerical aperture.
- To familiarize students on construction and types of optical fibers.
- To understand students, step and graded index fibers.
- To provide information on advantages of optical fibers

Teaching AIDS: PPTs, Black boardTime Management of Class: 150 min

5 mins for taking attendance10 min for revision of previous class.120 min for the lecture delivery15 min for doubts session

Refer assignment- V & tutorial-V sheets.

Da. SK. Ummaz Pasha - 1	
D.R. Sivanagi Reddy Emani - 🖉	
D.s. UU.Prably - Life	

Signature of faculty



LESSON PLAN (U-V)

Lesson No: 08

Duration of Lesson: 1hr 40 min

Lesson Title: losses in optical fiber, optical fiber for communication system, applications of optical fiber.

Instructional / Lesson Objectives:

- To make students understand losses in optical fibers.
- To familiarize students on communication systems in optical fibers.
- To understand student applications of optical fibers

Teaching AIDS	: PPTs, Black board
Time Management of Class	:100 min

10 mins for taking attendance15 for revision of previous class60 min for lecture delivery15 min for doubts session

Refer assignment- V & tutorial-V sheets.

Da. SK. Ummaz Pasha - 10
D.R. Si Vanagi Reddy Emani - 🖉
Ds. UU.Prabhy - Mar

Signature of faculty



ASSIGNMENT – 1

This Assignment corresponds to Unit No. 1

Question No.	Question	Objective No.	Outcome No.
1	Demonstrate Newton's rings Experiment with neat diagram and derive expression for calculation of radius of curvature of Plano convex lens.	1	1
2	Explain construction and working of Nicol prism and mention its applications.	1	1
3	Apply the concept of path difference to explain the bright and dark conditions of Interference in thin films by reflection.	1	1

Da. SK. Ummaz Pasha - 1
D.R. Sivanagi Reddy Emani - 🖉
Ds. UU.Prabhy -

Signature of HOD Date: 5-02-2024



ASSIGNMENT – 2

This Assignment corresponds to Unit No. 2

Question No.	Question	Objective No.	Outcome No.
1	Develop expression for one dimensional Schrödinger time independent wave equation.	2	2
2	Explain Kronig-Penny model with neat diagram	2	2
3	Demonstrate Davisson-Germer experiment with neat diagram mention its significance.	2	2



Da. SK. Ummaz Pasha - Ve
D.R. Sivanagi Reddy Emani - 🕹
D.s. UU.Prabhy - ift

Signature of HOD Date: 5-02-2024



ASSIGNMENT – 3

This Assignment corresponds to Unit No. 3

Question No.	Question	Objective No.	Outcome No.
1	what is Hall Effect and develop an expression for Hall coefficient (note illustrate with neat diagram.	3	3
2	Explain the V-I characteristics of P-N junction diode in forward and reverse bias conditions.	3	3
3.	Explain principle, construction, working and characteristics of LED and solar cell.	3	3

Da. SK. Ummaz Pasha - Un D.R. Sivanagi Reddy Emani - & D.s. UU.Prabhy

Signature of HOD Date: 5-02-2024



ASSIGNMENT – 4

This Assignment corresponds to Unit No. 4

Question No.	Question	Objective No.	Outcome No.
1	Explain sol-gel method & CVD method to synthesise nanomaterials with neat schematic diagram.	4	4
2	Explain synthesis of nanomaterials by using Ball milling with neat sketch and write its applications.	4	4
3	What is the principle behind the Transmission of Electron Microscope? Explain construction and working of TEM with neat sketch.	4	4



D.g. Sivanagi Reddy Emani - 🖉
D.s. UU.Prabhy -

Signature of HOD Date: 5-02-2024



ASSIGNMENT – 5

This Assignment corresponds to Unit No. 5

Question No.	Question	Objective No.	Outcome No.
1	Solve Einstein coefficients to demonstrate lasing action.	4	4
2	Analyze the operation of He-Ne Laser system using a neat energy level diagram	4	4
3	Explain acceptance angle and deduce the expression for numerical aperture.	4	4



Da. SK. Ummaz Pasha - Un
D.R. Si Vanagi Reddy Emani - 🕹
D.s. UU.Prabhy -

Signature of HOD Date: 5-02-2024



TUTORIAL – 1

This tutorial corresponds to Unit No. 1 (Objective Nos.: 1, Outcome Nos.: 1)

Q1. 1 The phenomena of interference of light have proved

A) Wave nature B) Particle nature C) Wave and Particle nature D) None of the above

Q2. What is the phase difference between two points situated on a wavefront?

A) $\pi/2$ B) 2π C) π D) 0

Q3. In Newton's Ring experiments, the diameter of dark rings is proportional to

A) Odd Natural numbers B) Natural Number

C) Even Natural Number D) Square root of natural number

Q4. Significant diffraction of x-rays can be obtained

A) by a single slit B) by a double slit C) by a diffraction D) by an atomic crystal

Q5. Polarised light can be produced by

A) reflection B) refraction C) Double refraction D) All of these



Signature of HOD Date: 5-02-2024

Dr. Sk. Ummar Pasha - Dr. Sivanagi Reddy Emani - 💰 D.s. UU.Prabhy



TUTORIAL – 2

This tutorial corresponds to Unit No. 2 (Objective Nos.: 2, Outcome Nos.: 2)

Q1. Dual nature [particle and wave] of matter was proposed by A) de Broglie B) Planck C) Einstein D) Newton

Q2. Which of the following phenomena cannot be explained by the classical theory? A) Photoelectric effect B) Compton effect C) Raman effect D) All the above

Q3. To electron gas, which of the following statistics is applicable? A) Maxwell–Boltzmann B) Bose–Einstein C) Fermi–Dirac D) Stefan–Hawking

Q4. The Kronig–Penney model is based on the assumption

A) Electrons move in a periodic potential field C) Electrons move in a zero potential field

B) Electrons move in a constant potential field D) Electrons move with constant potential energy

Q5. Classical free electron theory failed to explain

A) Specific heat of metals B) Thermionic emission C) Magnetic susceptibility of metals D) All the above

Signature of HOD Date: 5-02-2024

Da. SK. Ummaz Pasha - 10
D.R. Sivanagi Reddy Emaini - 😣
D.s. U.U.Prabhy -



TUTORIAL SHEET – 3

This tutorial corresponds to Unit No. 3 (Objective Nos.: 3, Outcome Nos.: 3)

Q1. Pure semiconductor behaves as an insulator at

A) 273 K B) -273 K C) 0 K D) None of these

Q2 N-type semiconductor is formed by adding impurity atoms to a pure semiconductor

A) trivalent B) penta valent C) zero valent D) tetra valent

Q3. Which type of semiconductor material has negative Hall coefficient A) p-type B) n-type C) intrinsic D) None of these

Q4. Which of the following devices convert light energy to electric energy?A) LEDB) Semiconductor laserC) Solar cellsD) Optical fibers

Q5. The main application of a Photodiode is

A) Light sensing B) Power regulation C) Signal amplification D) Energy storage



Signature of HOD Date: 5-02-2024

Dr. SK. Ummar. Pasha - Dr. Dr. Sivanagi Reddy Emain - & Dr. U U.Prabhy -



TUTORIAL – 4

This tutorial corresponds to Unit No. 4 (Objective Nos.: 4, Outcome Nos.: 4)

Q1. Quantum dot is an example of
A) one-dimensional nanomaterial C) two-dimensional nanomaterial
B) three-dimensional nanomaterial D) zero-dimensional nanomaterial
Q2. For a cubic nanoparticle of side 'a', surface area to volume ratio is given by
A) 3/ a B) 5/ a C) 4/ a D) 6/ a
Q3. Crystal structure of nanomaterials is known by
A) XRD B) CVD C) SEM D) PVD

Q4. The size range of nanomaterial is A) 1 to 100 Å B) 1 to 100 nm C) 1 to 100 mm D) 1 to 100 μ m

Q5. What is the standard form of TEM

A) Transmission Electron Microscope C) Transceiver Electrical Microscope

B) Transformer Electrode Microscope D) None of the above



Signature of HOD Date: 5-02-2024

D.a. Sk. Ummaz Pasha - W D.a. Sivanagi Reddy Emaini - & D.a. U U.Prabhy - Lifet

Signature of faculty Date: 5-02-2024



TUTORIAL SHEET – 5

This tutorial corresponds to Unit No. 5 (Objective Nos.: 5, Outcome Nos.: 5)

Q1. Laser has a high degree ofA) monochromacityB) coherenceC) intensityD) All of theseQ2. Numerical aperture represents______ capacity of a optical fiber.

A) light gathering B) light dissipation C) heat dissipation D) heat dissipation

Q3. Pick out the losses present in the optical communication system A) absorption losses B) scattering losses C) distortion losses D) All of these

Q4. Population inversion cannot be achieved by A) optical pumping B) chemical reaction C) electric discharge D) thermal process

Q5. In He–Ne laser, the ratio of He and Ne in gas mixture is A) 1:10 B) 10:1 C) 20:1 D) 1:20



Signature of HOD Date: 5-02-2024

D.R. Sivanagi Reddy Emani - O D.R. U U.Prabhy - Official



EVALUATION STRATEGY

Target (s)

a. Percentage of Pass : 85%

Assessment Method (s) (Maximum Marks for evaluation are defined in the Academic Regulations)

- a. Daily Attendance
- b. Assignments
- c. Online Quiz
- d. Continuous Internal Assessment
- e. Semester / End Examination

List out any new topic(s) or any innovation you would like to introduce in teaching the subjects in this semester

Case Study of any one existing application



Signature of HOD Date: 5-02-2024

Dr. Sk. Ummar Pasha - W Dr. Sivanagi Reddy Emani - & Dr. U.U.Prabhy - My



COURSE COMPLETION STATUS

Actual Date of Completion & Remarks if any **CSE-A**

Units	Remarks	Objective No. Achieved	Outcome No. Achieved
Unit 1	completed on 23.02.2024	1	1
Unit 2	completed on 17.03.2024	2	2
Unit 3	completed on 25.04.2024	3	3
Unit 4	completed on 06.05.2024	4	4
Unit 5	completed on 11.06.2024	5	5



Signature of HOD Date: 5-02-2024

Dr. Sk. Ummar Pasha - 10

Signature of faculty Date: 5-02-2024

CSE-B

Units	Remarks	Objective No. Achieved	Outcome No. Achieved
Unit 1	completed on 22.02.2024	1	1
Unit 2	completed on 15.03.2024	2	2
Unit 3	completed on 26.04.2024	3	3
Unit 4	completed on 04.05.2024	4	4
Unit 5	completed on 10.06.2024	5	5



Signature of HOD Date: 5-02-2024

D.E. Sivanagi Reddy Emari - &



Units	Remarks	Objective No. Achieved	Outcome No. Achieved
Unit 1	completed on 24.02.2024	1	1
Unit 2	completed on 16.03.2024	2	2
Unit 3	completed on 23.04.2024	3	3
Unit 4	completed on 06.05.2024	4	4
Unit 5	completed on 11.06.2024	5	5



Signature of HOD Date: 5-02-2024

D.g. U.U.Prabhy - Lifet

Signature of faculty Date: 5-02-2024

Mappings

1. Course Objectives-Course Outcomes Relationship Matrix

(Indicate the relationships by mark "X")

Course-Outcomes Course-Objectives	1	2	3	4	5
1	Н		М		
2		Н			
3			Н		
4				Н	
5					Н

2. Course Outcomes-Program Outcomes (POs) & PSOs Relationship Matrix

(Indicate the relationships by mark "X")

P-Outcomes C-Outcomes	PO- 1	РО- 2	РО- 3	РО- 4	РО- 5	PO-6	PO-7	PO-8	PO-9	РО- 10	PO- 11	PO- 12	PSO 1	PSO 2
1	Н			М										
2	Μ	Н	Μ											
3	Н													
4	М	L	Μ	L										
5	Н	L		Μ	Μ									

H-HIGH M-MODERATE L-LOW



Rubric for Evaluation

Performance Criteria	Unsatisfactory	Developing	Satisfactory	Exemplary
	1	2	3	4
Research & Gather Information	information that information some		Collects some basic Information most relates to the topic	Collects a great deal of Information all relates to the topic
Fulfill team role's dutyDoes not perform any duties of assigned team role.		Performs very little duties.	Performs nearly all duties.	Performs all duties of assigned team role.
Share Equally	Share EquallyAlways relies on others to do the work.Rarely does the assigned work - often needs reminding.		Usually does the assigned work - rarely needs reminding.	Always does the assigned work without having to be reminded
Listen to other team mates	never allows anyone life ta		Listens, but sometimes talks too much.	Listens and speaks a fair amount.



AP Mid exam papers

	An Autonomous Institution Anenthegiri (V&M), Koded, Survepst (DL), Telan (Approved by AICTE, New Delhi & Affiliated to JNTUH) I B.TECH II SEMESTER I MID EXAMINATIONS - APRIL 20		
	h : B.Tech. (CSE & CSE-AIML) Subject : Applied Physics, AP202BS 01.04.2024	Max. Marks: : Time: 120 Min	
	<u> PART - A</u>		
NSWEI	R ALL QUESTIONS	10 X 1	M = 10M
Q.No	Question	CO	BTL
1.	Brewster's law in terms of refractive index (μ) can be expressed ($~$) as	CO1	L1
	(A). $\mu = \sin i_p$ (B). $\mu = \tan i_p$ (C). $\mu = \cos i_p$ (D). $\mu = \cot i_p$		
2.	In Newton's Ring experiments, the diameter of dark rings is () proportional to	CO1	L1
	(A). Odd Natural numbers (B). Even Natural Number (C). Even Nat root of natural number	ural Number	(D). Squa
3.	In Newton's rings, the central spot in reflection mode is ()	CO1	L2
	(A). Always bright (B). Always dark (C). Bright or Dark (D). of b	lue colour	
4.	(A). Always oright (B). Always dark (C). Bright of Dark (D). of b Huygens wave theory of light cannot explain ()	CO1	L1
٦.		arization	LI
5.	First Brillouin zone corresponds to K value extending from ()	CO2	L2
	(A). $-\frac{3\pi}{a} to + \frac{3\pi}{a}$ (B). $-\frac{2\pi}{a} to + \frac{2\pi}{a}$ (C). $-\frac{\pi}{a} to + \frac{\pi}{a}$ (D). $-\frac{\pi}{a} to + \frac{2\pi}{a}$	002	22
6.	Dual nature [particle and wave] of matter was proposed by ()	CO2	L1
	(A). de Broglie (B). Einstein (C). Planck (D). Newton		
7.	To electron gas, which of the following statistics is applicable? ()	CO2	L3
	(A). Maxwell-Boltzmann (B). Fermi-Dirac (C). Bose-Einstein (D). Stefan-Haw	king
8.	The Kronig–Penney model is based on the assumption ()	CO2	L2
	 (A). Electrons move in a periodic potential field (B). Electrons move in (C). Electrons move in a zero potential field (D). Electrons move with constant potential energy 	n a constant po	otential fiel
9.	Which type of semiconductor material has negative Hall () coefficient	CO3	L2
	(A). p-type (B). n-type (C). intrinsic (D). None of these		
10.	Fermi level in N-type semiconductor lies between ()	CO3	L2

14.

15.

16.



Department of Humanities and Sciences

<u> PART - B</u>

ANSWEF		$4 \ge 5 \le 20 \le 10^{-10}$		
Q.No	Question		СО	BTL
11.	Analyse the intensity maxima and minimum conditions of Fraunhofer Diffraction at single slit with necessary derivation.		CO1	L4
12.	Analyze and describe the intensity distribution of a Fraunhofer diffraction of a single slit.		CO1	L4
13.	Demonstrate Davisson-Germer experiment with neat diagram mention its significance.		CO2	L3
Distinguish t level diagran	he solids based on band theory with neat energy ns.	CO2	L2	
Differentiate between intrinsic and extrinsic semiconductors CO3 with energy level diagram.				
what is Hall coefficient (r with neat dia	L3			







I B.TECH II SEMESTER II MID EXAMINATIONS - JUNE 2024

Branch : B.Tech. (CSE & AIML)		Max. Marks : 30M
Date : 18-Jun-2024	Session : Afternoon	Time : 120 Min
Subject : Applied Phy	ysics,AP202BS	

PART - A

ANSWEI	R ALL THE QUESTIONS	10 X 1M	[= 10M
Q.No	Question	СО	BTL
1.	The function of a BJT (Bipolar Junction Transistor) is()(A). Amplify signals(B). Regulate voltage(C). Generate alternating currentenergy(B)(B)	CO3 (D). Stor	L1 e
2.	The working principle of a LED is ()	CO3	L2
	(A). Photoelectric effect (B). electroluminescence (C). Photovoltaic effect (breakdown	D). therma	ıl
3.	For a cubic nanoparticle of side 'a', surface area to volume ratio is given () by	CO4	L2
	(A). 3/ a (B). 4/ a (C). 5/ a (D). 6/ a		
4.	Quantum dot is an example of ()	CO4	L1
	(A). one-dimensional nanomaterial (B). three-dimensional nanomaterial (C). t nanomaterial (D). zero-dimensional nanomaterial	two-dimen	sional
5.	The size range of nanomaterial is ()	CO4	L1
	(A). 1 to 100 Å (B). 1 to 100 mm (C). 1 to 100 nm (D). 1 to 100 µm		
6.	Widespread use of nano technology is due to ()	CO4	L2
	(A). Small scale miniaturization (B). The fact that it is faster and cheaper (C). (D). All the above	Its lower	cost
7.	The refractive index of core and cladding are 1.563 and 1.498 () respectively and then numerical aperture (NA) is	CO5	L2
	(A). 0.346 (B). 0.199 (C). 0.246 (D). 0.446		
8.	If an electron excites from lower state to higher state then that process is () called	CO5	L2
	(A). spontaneous emission (B). stimulated emission (C). absorption (D). sys	tematic er	nission
9.	Step index fiber can be a ()	CO5	L1
	(A). multimode fiber only (B). monomode fiber only (C). monomode as well fiber (D). either monomode or multimode (cannot be both)	as multim	ode
10.	Numerical aperture represents capacity of a optical fiber. ()	CO5	L2
	(A). light gathering (B). heat dissipation (C). heat absorption (D). light dissi	pation	

15.

16.



Department of Humanities and Sciences

PART - B ANSWER ANY FOUR $4 \ge 5M = 20M$ со Q.No Question BTL L3 What is photo diode?. Explain the principle, working and characteristics CO3 11. of photo diode. Discuss the V-I characteristics of zenar diode under forward & reverse CO3 L4 12. bias conditions. Mention at least 2 differences between ordinary P-N junction diode and zenar diode. L3 13. Explain construction and working of Scanning Electron Microscope CO4 (SÊM) with neat diagrams. L3 14. Explain sol-gel method to synthesis nanomaterials with neat schematic CO4 diaaram Solve Einstein coefficients to demonstrate lasing action CO5 L3 Explain the construction and working of Nd-YAG laser. CO5 L4

55



Continuous Internal Assessment (R-22)

Internal Marks (CSE-A)

Programme: B Tech		Year: I	Cour	se: Theory	A.Y: 2023-2	A.Y: 2023-24		
Course: Applied Physics		Section: CSE A		Faculty Name: Dr. SK.UMMAR PA				
S. No	Roll No	MID-I (35M)	MID-II (35M)	Avg. of MID I & II	Viva- Voce/Poster Presentation (5M)	Total Marks (40)		
1	22C11A0549	20	9	15	4	19		
2	22C11A05H5	18	5	12	3	15		
3	23C11A0501	19	16	18	5	23		
4	23C11A0502	35	34	35	5	40		
5	23C11A0503	22	19	21	3	24		
6	23C11A0504	16	14	15	4	19		
7	23C11A0505	19	12	16	3	19		
8	23C11A0506	29	26	28	4	32		
9	23C11A0507	34	26	30	5	34		
10	23C11A0508	17	13	15	5	20		
11	23C11A0509	35	35	35	5	40		
12	23C11A0510	34	30	32	5	37		
13	23C11A0511	31	26	29	4	33		
14	23C11A0512	16	19	18	4	22		
15	23C11A0513	35	34	35	5	40		
16	23C11A0514	15	13	14	А	17		
17	23C11A0515	28	21	25	4	29		
18	23C11A0516	17	23	20	3	23		
19	23C11A0517	24	19	22	4	26		



Department of Humanities and Sciences

				annues and sei		
20	23C11A0519	31	29	30	5	36
21	23C11A0520	24	24	24	4	28
22	23C11A0521	34	28	31	5	36
23	23C11A0522	35	33	34	5	39
24	23C11A0523	28	22	25	А	25
25	23C11A0524	23	18	21	5	26
26	23C11A0525	23	0	12	3	14
27	23C11A0526	33	33	33	5	38
28	23C11A0527	20	26	23	4	27
29	23C11A0528	29	22	26	3	29
30	23C11A0529	27	28	28	4	32
31	23C11A0530	27	21	24	4	29
32	23C11A0531	17	17	17	4	19
33	23C11A0532	17	19	18	3	19
34	23C11A0533	15	15	15	5	18
35	23C11A0534	24	32	28	5	33
36	23C11A0535	33	31	32	5	37
37	23C11A0536	33	34	34	5	39
38	23C11A0537	24	18	21	4	25
39	23C11A0538	30	22	26	5	31
40	23C11A0539	17	15	16	3	19
41	23C11A0540	20	21	21	4	25
42	23C11A0541	20	16	18	5	23
43	23C11A0542	21	22	22	4	26
44	23C11A0543	28	25	27	5	32
45	23C11A0544	25	24	25	5	30



	Department of Humanities and Sciences								
46	23C11A0547	10	13	12	5	17			
47	23C11A0548	12	16	14	5	19			
48	23C11A0549	16	17	17	3	20			
49	23C11A0550	22	21	22	5	27			
50	23C11A0551	20	21	21	5	26			
51	23C11A0552	15	5	10	4	14			
52	23C11A0553	22	29	26	5	31			
53	23C11A0554	23	28	26	4	30			
54	23C11A0555	29	35	32	5	37			
55	23C11A0556	32	24	28	5	33			
56	23C11A0557	31	33	32	5	37			
57	23C11A0558	20	18	19	3	22			
58	23C11A0560	30	29	30	5	35			

No. of Absentees: 00

Total Strength: 58



Dr. Sk. Ummar Pasha - Un

Signature of HoD Faculty Signature of



Internal Marks (CSE-B)

Programme: B.Tech. (CSE)		Year: I	Course	: Theory	A.Y: 2023-24	
Course: Applied Physics		Section: B	Faculty	/ Name: Dr. Sivanagi	Reddy Emani	
S. No	Roll No	MID-I (35M)	MID-II (35M)	Avg. of MID I & II	Viva-Voce/Poster Presentation (5M)	Total Marks (40)
1	23C11A0561	24	16	20	4	24
2	23C11A0562	30	30	30	5	35
3	23C11A0563	28	22	25	4	29
4	23C11A0564	15	29	22	4	26
5	23C11A0565	22	16	19	4	23
6	23C11A0566	30	20	25	4	29
7	23C11A0567	29	22	26	4	30
8	23C11A0568	32	26	29	5	34
9	23C11A0569	23	23	23	5	28
10	23C11A0570	33	34	34	5	39
11	23C11A0571	AB	AB	AB	AB	AB
12	23C11A0572	27	17	22	3	25
13	23C11A0573	25	18	22	4	26
14	23C11A0574	24	19	22	4	26
15	23C11A0575	24	19	22	4	26
16	23C11A0576	30	34	32	5	37
17	23C11A0577	23	19	21	4	25
18	23C11A0578	34	27	31	5	36



Department of Humanities and Sciences

			par unent or r	fumations and S		
19	23C11A0579	30	18	24	4	28
20	23C11A0580	28	31	30	5	35
21	23C11A0581	25	17	21	4	25
22	23C11A0582	22	19	21	4	25
23	23C11A0583	21	13	17	4	21
24	23C11A0584	26	26	26	4	30
25	23C11A0585	30	33	32	5	37
26	23C11A0586	7	9	8	5	13
27	23C11A0587	23	30	27	4	31
28	23C11A0589	25	18	22	4	26
29	23C11A0590	35	35	35	5	40
30	23C11A0591	24	23	24	5	29
31	23C11A0592	26	26	26	4	30
32	23C11A0593	28	26	27	5	32
33	23C11A0594	9	13	11	5	16
34	23C11A0595	28	28	28	5	33
35	23C11A0596	30	20	25	5	30
36	23C11A0597	22	16	19	5	24
37	23C11A0598	15	14	15	4	19
38	23C11A0599	17	17	17	4	21
39	23C11A05A0	21	16	19	4	23
40	23C11A05A1	28	16	22	4	26
41	23C11A05A2	28	23	26	4	30
42	23C11A05A3	19	12	16	4	20
43	23C11A05A4	25	13	19	4	23
44	23C11A05A5	32	31	32	5	37



Department of Humanities and Sciences

		1	Depai intent	of muniantice	and belences	
45	23C11A05A6	27	21	24	4	28
46	23C11A05A7	23	16	20	4	24
47	23C11A05A8	28	5	17	4	21
48	23C11A05A9	32	AB	16	AB	16
49	23C11A05B0	27	AB	14	AB	14
50	23C11A05B1	26	20	23	3	26
51	23C11A05B2	20	18	19	3	22
52	23C11A05B3	28	22	25	5	30
53	23C11A05B4	26	24	25	5	30
54	23C11A05B5	30	30	30	5	35
55	23C11A05B6	29	30	30	5	35
56	23C11A05B7	27	14	21	4	25
57	23C11A05B8	29	24	27	4	31
58	23C11A05B9	23	14	19	4	23
59	23C11A05C0	28	21	25	5	30

No. of Absentees: 01

Total Strength: 59



Signature of HoD Faculty Dr. Sivanagi Reddy Emari - &

Signature of

Course File



Department of Humanities and Sciences

Internal Marks (CSE-C)

Programme: **B Tech**

Year: I

Course: Theory

A.Y: 2023-24

Course: APPLIED PHYSICS

Section: CSE A

Faculty Name: Dr. U U Prabhu

S. No	Roll No	MID-I (35M)	MID-II (35M)	Avg. of MID I & II	Viva-Voce/Poster Presentation (5M)	Total Marks (40)
1	23C11A05C1	23	25	24	4	28
2	23C11A05C2	26	16	21	1	22
3	23C11A05C3	26	21	24	3	27
4	23C11A05C4	35	35	35	5	40
5	23C11A05C5	14	19	17	1	18
6	23C11A05C6	32	34	33	5	38
7	23C11A05C7	20	18	19	2	21
8	23C11A05C8	23	23	23	3	23
9	23C11A05C9	16	19	18	2	20
10	23C11A05D0	24	25	25	4	29
11	23C11A05D1	15	18	17	1	18
12	23C11A05D3	30	27	29	5	34
13	23C11A05D4	13	14	14	2	16
14	23C11A05D5	14	9	12	2	12
15	23C11A05D6	25	23	24	5	29
16	23C11A05D7	14	16	15	1	15
17	23C11A05D8	18	19	19	3	22
18	23C11A05D9	14	21	18	1	19
19	23C11A05E0	16	19	18	2	20
20	23C11A05E1	16	10	13	2	15
21	23C11A05E2	30	33	32	3	35
22	23C11A05E3	14	16	15	1	16
23	23C11A05E4	23	28	26	1	27
24	23C11A05E5	8	16	12	2	14



Department of Humanities and Sciences

		Departin	icht of Huma	annues and Sci	lences	
25	23C11A05E6	16	18	17	2	19
26	23C11A05E7	20	21	21	1	22
27	23C11A05E8	13	17	15	1	16
28	23C11A05E9	13	16	15	1	16
29	23C11A05F0	14	16	15	1	16
30	23C11A05F1	10	26	18	4	22
31	23C11A05F2	25	34	30	2	32
32	23C11A05F3	17	16	17	3	20
33	23C11A05F4	21	23	22	3	25
34	23C11A05F5	15	18	17	1	18
35	23C11A05F6	10	16	13	3	16
36	23C11A05F7	16	17	17	1	17
37	23C11A05F8	8	15	12	3	15
38	23C11A05F9	10	16	13	2	15
39	23C11A05G0	9	AB	5	AB	5
40	23C11A05G1	16	16	16	3	19
41	23C11A05G2	13	17	15	2	17
42	23C11A05G3	20	20	20	2	22
43	23C11A05G4	13	17	15	2	17
44	23C11A05G5	19	16	18	4	22
45	23C11A05G6	14	15	15	2	17
46	23C11A05G7	20	15	18	2	20
47	23C11A05G8	16	14	15	1	16
48	23C11A05G9	30	29	30	4	34
49	23C11A05H0	17	23	20	1	21
50	23C11A05H1	17	16	17	4	21
51	23C11A05H2	16	15	16	1	17
52	23C11A05H3	17	16	17	3	20
		•	•	•	•	·



	Department of Hamannes and Sciences							
53	23C11A05H4	17	15	16	1	17		
54	23C11A05H5	22	15	19	2	21		
55	23C11A05H6	19	17	18	2	20		
56	23C11A05H7	24	31	28	4	32		

No. of Absentees: 01

Total Strength: 56

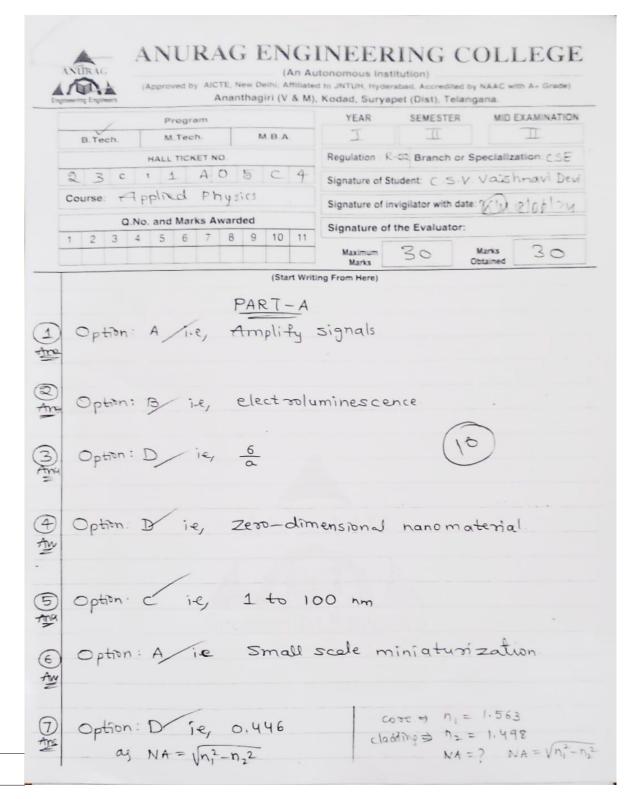
Signature of HoD Faculty

D.s. U.U.Prathy - Lifet

Signature of



Sample Mid Exam Answer scripts





PART-B Photo Diode Photo Diode is a projunction diode that mas operates in reverse bias condition It takes source and after performing action it e electricity Principle: The principle of photo divole is -photoconductive mode " of operation. Working & Construction: Connection P-type Depletion O->hole Regin 9-Jelectron h-type (+) connection The construction of photo dode consists of h-type semiconductor material on that a t p-type semiconductor is placed Then, we observe i.....

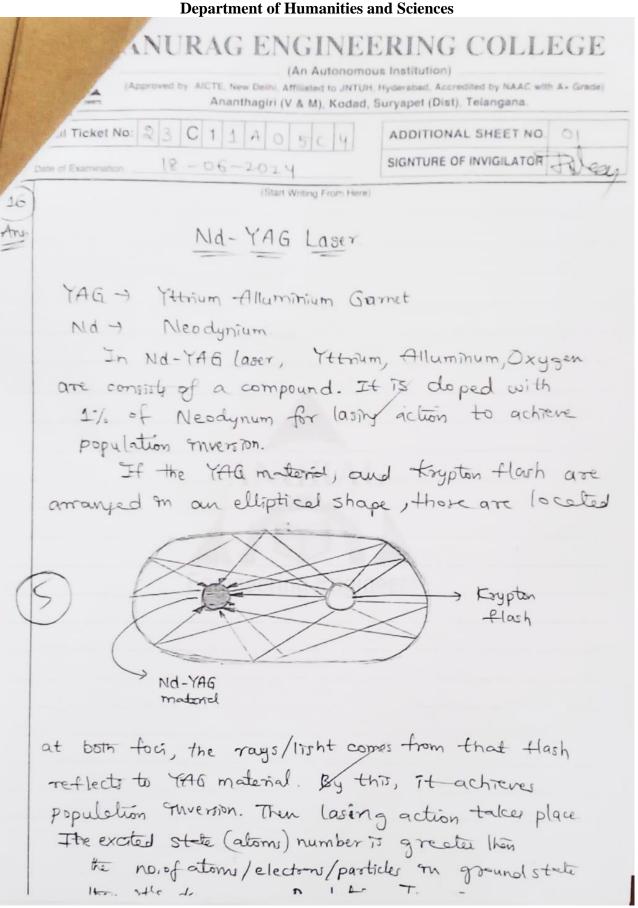


Sol- Gel Method Sol-Gel method to one type of Bottom- Up Approach to fabricate the nanomaterials. In this, there are silice gels, zirconium gels, etc. are formed We use some materials to form those gets For example; Tetra methoxy Silane, Tetra Ethoxy silane materials are used to get silica gets Some oxides like Tio2, SiO2, Zro2 are synthesized by this Sol-Gel Method In this method, there are 4 stages 1. thy dooly si 2 Condensation .. 3. Growth of particles 4 Agglomeration of particles. * 1 Hydrolysis The process of -- Addition of water is called "Hydrolyni To the repursed presurer/material add water that can replace "OR" group with "OH" grou Exa MOR + H20 -> MOH + ROH If we see the above reaction, MOR is replaced MOH. This can be done in this stage of "Hydro! * 2. Condensation. Tru reaction

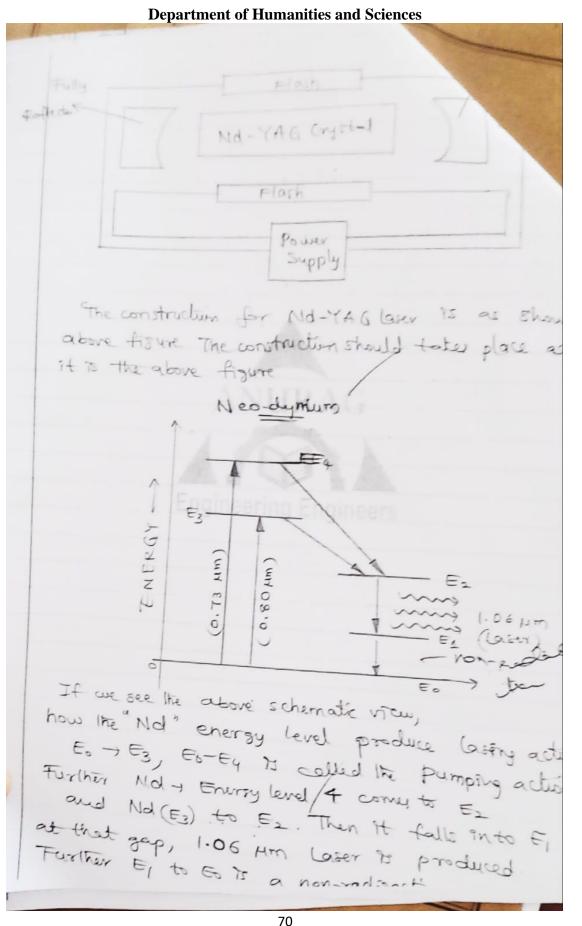


office this stage the material gel ". * 384 Growth & Agglomeration If we leave this for some time, then the between the gel are become stronger & st This is called "Aging." Conden-Pro 0 0 Gran 10/10 A. A Sol Gel A flar condensations Superioritical is Thermal Xerogel 000 50 5-450 Freeze Cryogel Characteristics / Advantage:-* Simple Method * Eco-friendly * Punity of productivity * High efficiency + Low cost * The obtained name particles like (Cry Co, An E AIT Used many plan, i 4











ince of Internations Absorption 11, Spontaneous Envirsion III Stimulated Emission From these three types, we get "3" different "rate of contrait " values Thore are -R12 = B12 PUN, - D(-from Absorption) Rai = Azi N2 - (InSportaneous Frittion) Ray = Bai Na Py (D) (from Stimulated Emirine) I = I + II / $R_{12} = R_{21}(p) + R_{21}(pt)$ B12 PVN, = A21 N2 + B21 N2 PV $B_{12} P_{V} N_{1} - B_{21} P_{V} N_{2} = A_{21} N_{2}$ $P_{v}(B_{12}N_{1}-B_{24}N_{2}) = A_{24}N_{2}$ $P_{v} = \frac{A_{21} N_{2}}{(B_{12} N_{1} - B_{21} N_{2})} - (1)$ Divide (B12 N2) on numerator & denominator of eg. () on RHS $= \rho_{y} = \frac{A_{21} N_{2}}{B_{12} N_{2}}$ $\left(\frac{B_{12}N_1}{B_{12}N_2} - \frac{B_{24}N_2}{B_{12}N_2}\right)$ $P = \frac{(A_{21}/B_{12})}{B_{12}}$ 1

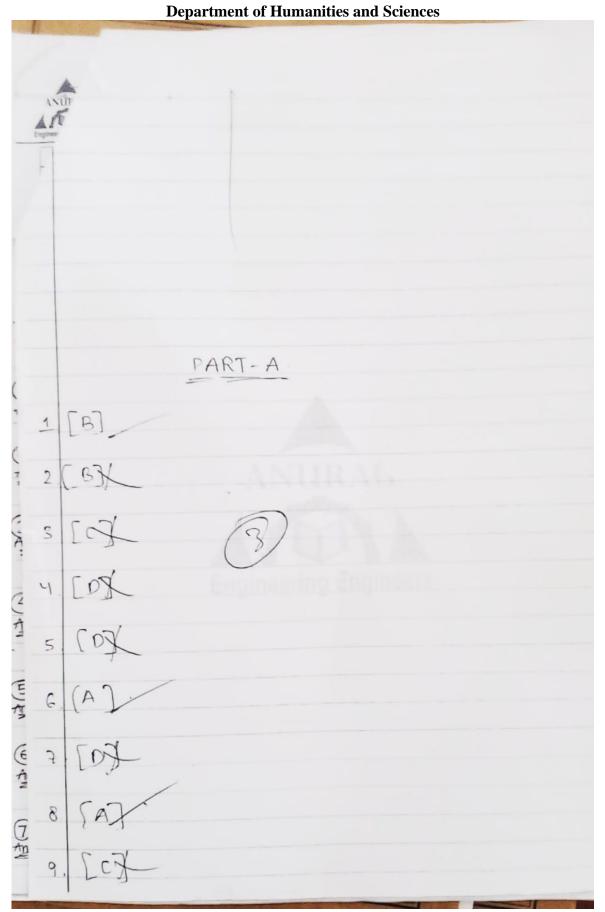


Ananthagiri (V & M).	t to JNTUR, Hyderabad, Accredited by NAAC with A+ Grade) Kodad, Suryapet (Dist), Telangana. YEAR SEMESTER MID EXAMINATION
Program	TEAR SEMESTER MID ECOMPONIE
B.Tech M.Tech M.B.A.	Regulation 27 Branch or Specialization
ALL TICKET NO	
	Signature of Student Ch. Srikaro
course: Applied payales	Signature of invigilator with date of tube
Q.No. and Marks Awarded	Signature of the Evaluator: 100
1 2 3 4 5 6 7 8 9 10 11	Maximum 30 Marks 3 Marks Obtained
(Start Wri	ting From Here)
	in a lastar
I Intrinsic (1- THE) Ser	niconductor
Tothingic (P-TYPE) Ser	ductor the majority d
is TO the F. Type semicor	ductor the majority or
is In the P. Type semicor the current formed by	the atoms like Al
is TO the F. Type semicor	the atoms like Al
the current formed by	the atoms like Al
i) In the P-Type semicor the current formed by (i) In the P-Type semicor level is very less of	the atoms like Al
i) In the P-Type semicor the current formed by ii) In the P-Type semicor level is very less of iii) In the P-Type semi	the atoms like Al
i) In the P-Type semicor the current formed by (i) In the P-Type semicor level is very less of (ii) In the P-Type semi (iii) In the P-Type semi bond is formed.	conductor the heralent
i) In the P-TYPE semicor the current formed by ii) In the P-TYPE semicor level is very less of iii) In the P-TYPE semi bond is formed. (iv) In the P-TYPE fem	conductor the heralent
i) In the P-TYPE semicon the current formed by ii) In the P-TYPE semicon level is very less of iii) In the P-TYPE semi hond is formed. (iv) In the P-TYPE fem	conductor the heralent
i) In the P-Type semicor the current formed by (i) In the P-Type semicor level is very less of (ii) In the P-Type semi (iii) In the P-Type semi bond is formed.	conductor the heralent
i) In the P-TYPE semicor the current formed by ii) In the P-TYPE semicor level is very less of iii) In the P-TYPE semi bond is formed. (iv) In the P-TYPE fem	conductor the heralent
i) In the P-TYPE semicor the current formed by ii) In the P-TYPE semicor level is very less of iii) In the P-TYPE semi bond is formed. (iv) In the P-TYPE fem	conductor the heralent
i) In the P-Type semicor the current formed by (i) In the P-Type semicor level is very less of (ii) In the P-Type semi bond is formed. (iv) In the P-Type fem represented by EC.	iconductor the atoms are
(1) In the P-Type semicor the current formed by (1) In the P-Type semicor level is very less of (11) In the P-Type semi bond is formed. (11) In the P-Type fem represented by EC.	conductor the heralent
i) In the P-Type semicor the current formed by ii) In the P-Type semicor level is very less of iii) In the P-Type semi bond is formed. (iv) In the P-Type ferm represented by EC.	iconductor the atoms are
i) In the P-Type semicor the current formed by (i) In the P-Type semicor level is very less of (ii) In the P-Type semi bond is formed. (iv) In the P-Type fem represented by EC.	iconductor the atoms are
(1) In the P-Type semicor the current formed by (1) In the P-Type semicor level is very less of (11) In the P-Type semi bond is formed. (12) In the P-Type fem represented by EC.	ductor the majority of the atoms like Al. anductor the Energy conductor the heralent iconductor the atoms are



(iii) In N- Type semiconductor the covelent bond is formed. (it) In N- Type semiconductor the atoms are represented by Ep volonced bord FD A 1a. Ant bi SL 0 Engineering Engineers Path difference = . e + dsing. phase difference = 27 (e+dsing) R= asin n2 TT (e+dsino) 21 (1+d sing) $\frac{2\pi}{2\pi} \left(e + deine \right) \left(\frac{2\pi}{2} \left(e + deine \right) \right)$







Sample Assignments

Applied Physics Mid-2. Assignment Name: Saissikerman P H.T.NO: 2301170506 Branch; CSE Section : C

ANS

25 =5



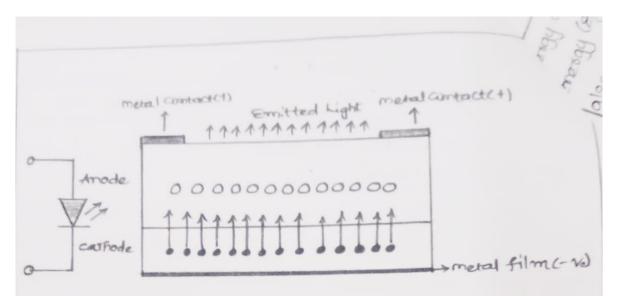
ScillA0506 Suignikumar P 09-0 Explain The principle, construction, working and characteristics of a light emitting diade cher) and golar cell with macessary diagrams. A hight smitting Diade cherD:

-AP ASSIGNMENT

The principle behind WED is electroluminisconde. A WED is specially made-forward biased PN junction dide They emit spontaneous radiation in UV, Visible and infrared regions. Semiconductors having energy band gap larger than this limit must be used. For visible WED, Galliam assenide and galliam prospide are used, which are transportant. Here GaAs emits are used, which are transport. Here GaAs emits are or green, Ga entres ared or yellow, GaP emits are or green, Ga entres have light. WED's are fabricated from GaP and Gatsp. NED's greate at low voltages and arovents, typically at 1.5V and 10mA.

Construction: At first an N-type layer is grown on a substance and them a P-type layer is deposited on it by The process of diffusion. Metal contacts (Amade) are more at the outers edge of the P-kayers so that more appen surface is left free for light to escayoe. For making cathede connections, a metal film is coated at the bottom of the substrate. This film also reflects as much light as passible to the surface of the device.





working:

On forciariod biasing a WED, The majority anniers present in The respective regions of diode across the p-n junction. The free electrooms at the m-side move taccords p-side and holes-from p-side move tocords The m-side of The diode. The free electrooms That enter The p-side from the m-side are called minority charge coronarions in the program and vice versa, This marcoses the local mimority arrivers population than the mormal value. This is known as mimority consiers injection The excess minosity arrivers diffuse away from The junction and produce recombination with majority consideres. Fors example the excess minority electron in The conduction band of The progion recombine with the majority holes in the valence band of the prolegion recombine with the majority holes. and emit photons. these the electrons make downwood transistion from conduction band to valence barnd for recombination with holes and the difference



angy will be emitted in the form of photons of margy (Eg). Smiller action takes place in the marging also. Unders reverse Bias, no photons are emitted. It is essential that light should be comitted from One side of the junction and most of the light emitted shalld come Out of the darke. For this the derice is made of an asymptotically doped junction. The impersity concentration in the m-region should be highers than in the provegion so that injection of conners proceeds in one direction. Light output. FIF (MA) Solar Celli promoiple: A photovoltaic cell or solars cell is nothing but a p-n junction device based on the primciple of photovottaic effect. It directly converts light into electroloty. Construction and working: The cell is a p-njunction diade with doped semiconductors. Doping of m junction is very high in junction is made very thin so that light redictions can penetrate the junction. Its coorking is similars to photodiade execpt that solars cell do not require any external voltage biasing.



I Explain 301-gel method and chemical Vapouro Deposi frion methods of synthesising mano materials with meat Schematic Diagram. A' Sol-Gel method: rusing the sol-gel method, silica gets, zircomia and yttaicon gets and atomino silicate gets are formed. The continuous porosity at the manoscale is used as a place for loading eacondary materials This method has The ability of synthesizing many mineral onlides such as Tio2, SiO2 and to 02. Sol is particles in a liquid. A colloid That is suspended in a liquid is called a Sol. Sol-gel-formation acres in four stages: i) Hydrolysis ii) ander sation iii) Growth of particles and integlomeration of particles. The preakson for synthesizing these colliads ameists of ions of metal oxide, alkoxides and aloxy silanes. For preparation of alumina and zirscomia, aluminium proposide and streamium proposide are used respectively as preatosor. i) tydoohysis: During hydrophysis, addition of obatero results in the replacement of [OR] calky or alkoxy group bonded to the oxygen atom with COH-] (hydroxy) graup which is a functional grooup consisting oxygen]. Hydrolysis ocaros by attack of Oxygen on silicon atoms in silica gel. Hydroolysis com be accelerated by adding catalyst



get is placed in the atmospherie afters production to day spontaneously. The get obtained from this method is called reroget. In the second method, balled supercroition method, The material obtained from this method has produle metworks and low strength and is "hollow". This product is called herocel. Acrogels are said to be the lightest and least dense solids, so that about 50-95% of it's volume is are. The accepts are known as the best Thermal grylation material. The basic process of Sol-gel method: Hydrolyze 00000 condense precutosors —> Solution 201 Gel.



dagen (Ha), Nitragen (Na), Aragon, Helium gases are bed as caronian gos to carry procursions and other gases inside the chambers. carroier gas do not involve in any reactions inside The chamber. In godes- to deposit Alicon diaxide, procurses used are silane (siH4) and Oxidizing gas used is 02. sity + 02 -> sio2+2H2. Similarly, if we want to bond silicon to a subface (Substrate) we may use a trachloso slone (SiHclz) as preatoson, when The troichloso silane is heated in The Coating characters the decomposition and coating reaction may look like This. sitcla > sitcle the In This method complete samples of any shape cambe coasted as shown in Fig unlike PUD metho where only directly exposed prit of substrate are deposited. CVD Past to be PVD coated.



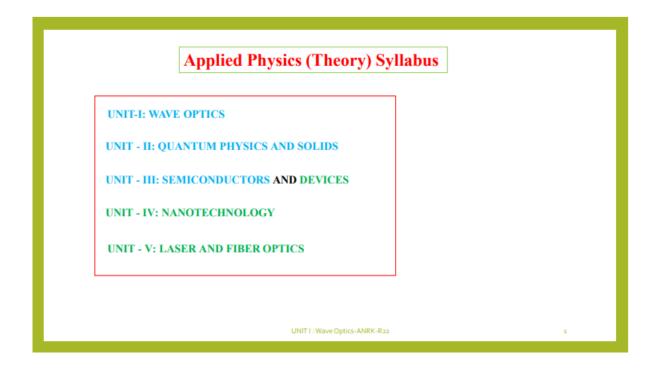
2) with the help of diagram discuss in detail the re sero, techniques of mano material characterisas 41 SRD: & Ray Diffraction XRD is a technique used to determine The exystal stoucture of a material. It involves shiring on K-romy beam at a sample and measuring the ang and intensities of The diffracted beams. Through and used to produce The difficaction pattern because their convelongth & is often the same order of magnitude as The spacing, d, between The onystal plomes [1-100A°]. The results of an array study of sample are usually presented as a plot of reflected intensities versus detected angle 20, called as diffraction pattern, 2d Smg=n ghtensity 20 In a x-rray diffractometers, different existalline phases give different diffraction patterns. Phase Idartification can be persformed by comparing x-roay diffraction patterns. Phase identification are be



Course materials like Notes, PPT's, etc.

Will be attached.

Sample PPT:





Sample Notes:

UNIT-I: WAVE OPTICS

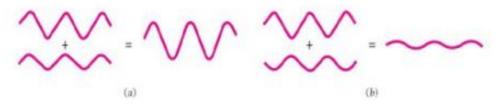
Optics is the branch of physics in which we study the nature of light and the phenomenon exhibited by it. On the basis of wave nature of light we can explain the phenomena of interference, diffraction and polarization (also called wave optics). However, photoelectric effect and Compton effect can be explained by particle nature of light.

Huygen's principle

The wave theory of light was first put forward by Christian Huygens in 1678. Huygen's suggested that light creates periodic disturbance which travels as waves in a manner very similar to that of sound waves. He gave the concept of wavefront. A wavefront refers to an imaginary surface containing points that are in phase—that is, points that have the same phase or displacement from equilibrium—at any given time during the propagation of a wave. According to this theory, every point on a wavefront serves as the source of secondary spherical wavelets. The envelope formed by these secondary wavelets at any given moment represents the new position of the wavefront.

Superposition of waves

When two or more waves of the same nature travel past a point at the same time, the instantaneous amplitude there is the sum of the instantaneous amplitudes of the individual waves.



When two or more trains of light waves meet in a region, they interfere to produce a new wave there whose instantaneous amplitude is the sum of those of the original waves. Constructive interference (fig. a) refers to the reinforcement (adding) of waves with the same phase to produce a greater amplitude, and destructive interference (fig.

b) refers to the partial or complete cancellation of waves whose phases differ (opposite phases).

If y_1 and y_2 are the displacements of the two waves, then the resultant displacement y is given by



SEMICONDUCTORS & DEVICES

Semiconductor Fundamentals: -

→ The materials whose electrical properties lie between those of conductors and Insulators are known as semiconductors.

→ The examples of such materials are germanium (Ge), Silicon (Si), gallium arsenide (Ga As), Cadium Sulfide (Cds), lead telluride etc,.

 \rightarrow At absolute zero temperature (ie at 0K) there are no electrons in the conduction band of semiconductors and the valence band is completely filled. Thus the semiconductor behaves like an insulator at 0K.

→ If the temperature is increased the width of the energy gap reduces, consequently, some of the electrons jump into condition band and semiconductors show some conductivity.

 \rightarrow It is thus obvious, that the conductivity of semiconductors increases with the increases in temperature.

Commonly used semiconductors: -

→ The most frequency used materials are germanium (Ge), and Silicon (Si).

 \rightarrow It is because then energy required to break their co-valent bonds is every small; being 0.7 eV for Ge and 1.1 eV for Silicon.

Chemically pure semiconductors are known as intrinsic semiconductors. A semiconductor is considered to be pure when there is less than one impurity atom in a billion host atoms.

At 0K an Intrinsic Semiconductor Behaves as a Perfect Insulator. As all the valence electrons are engaged in covalent bonds, the bonds are complete. The energy available at 0K is not sufficient to break the covalent bonds.

LIMITATIONS OF INTRINSIC SEMICONDUCTOR

Intrinsic semiconductors are not useful for device manufacture because of low conductivity and the strong dependence of conductivity on temperature. 4



Department of Humanities and Sciences

UNIT - IV: NANOTECHNOLOGY

Nanoscale, quantum confinement, surface to volume ratio, bottom-up fabrication: sol-gel, combustion methods, top-down fabrication: ball milling. physical vapor deposition (PVD), Chemical vapor deposition (CVD), Characterization techniques - XRD, SEM & TEM, applications of nanomaterials.

The term nanotechnology was first coined in 1974 by Norio Taniguchi of the Tokyo Science University. Nanoscience is the study of objects having size less than hundred nanometers at least in one dimension, whereas nanotechnology is the engineering of these objects using different techniques. Nanotechnology is all about the techniques and tools to come up with a nanoscale design or system. It all started with a lecture "There's Plenty of Room at the Bottom" delivered by Richard P. Feynman on December 29, 1959 in which he predicted the possibilities of manipulating atoms and making atomic level machines.

Nano is a Greek word that means dwarf (small). On the other hand, **nanotechnology** is a branch in which we study the design, characteristics, production and application of structure, devices and systems on the nanoscale.

The materials developed under nanotechnology show very different properties at nanoscale in comparison to macroscale though the properties hardly change at microscale. For instance, opaque substances at macroscale become transparent at nanoscale (Cu). Materials having inert properties attain catalytic properties (Pt), stable materials turn into combustible materials (Al), solids turn into liquids (Au), insulators become conductors (Si), etc.

Nanoscale

The prefix nano in the word nanotechnology means a billionth $(1 \times 10-9)$. Materials with at least one of the dimensions measuring less than 100 nm are known as nanomaterials. We define nanomaterials as those which have a characteristic length scale within about 100 nm. One nanometer spans 3 to 5 atoms lined up in a row. For comparison, a single human hair is about 80,000 nm wide, Water molecules is about 0.3 nm. Diameter of (human) DNA strand 2.5 nm, and a red blood cell is approximately 7,000 nm wide. The manoscale, may be taken as 0.2 nm to 100 nm.



UNIT 5 LASER AND FIBER OPTICS

The word 'LASER' is the acronym for Light Amplification through Stimulated Emission of Radiation. Einstein gave the theoretical basis for the development of laser in 1916, when he predicted the possibility of stimulated emission. In 1954, C. H. Townes and his co-workers put Einstein's prediction for practical realization. They developed a microwave amplifier based on stimulated emission of radiation. It was called a maser. Shortly thereafter, T. H. Maiman built the first laser device in 1960. In 1961, A. Javan and associates developed the first gas laser, the helium-neon laser.

ABSORPTION AND EMISSION OF RADIATION

Absorption An atom or molecule in the ground state E_1 can absorb a photon of energy hv and go to the higher energy state E_2 . This process is known as absorption.



The rate of upward transition R_{12} from ground state E_1 to excited state E_2 is proportional to the population of the lower energy level N_1 (number of atoms per unit volume) and to the energy density of radiation ρ_v

$$R_{12} \alpha \rho_{\nu}$$
$$\alpha N_{1}$$
$$R_{12} = B_{12} \rho_{\nu} N_{1}$$

where proportionality constant B12 is known as the Einstein's coefficient of absorption of radiation.

Normally, the higher energy state is an unstable state and hence, the atoms will make a transition back to the lower energy state with the emission of a photon. Such an emission can take place by one of the two methods given below.